

Lecture 11: High Swing Current Sources

Announcements:

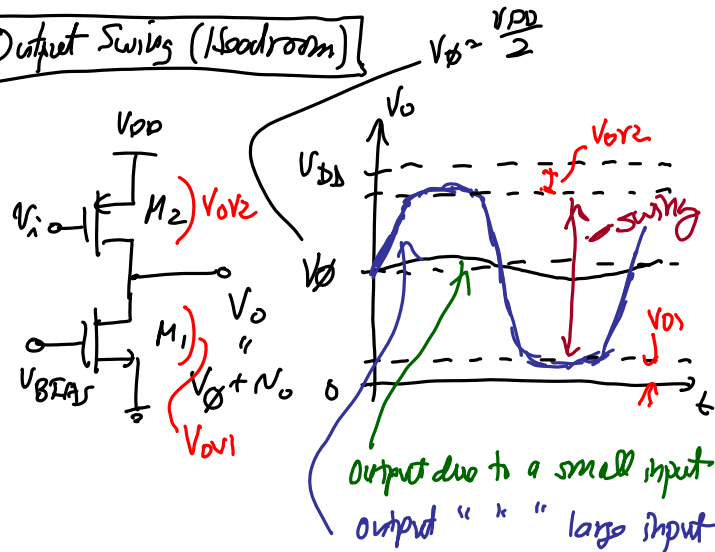
- ↪ HW#5 online
- ↪ Lab#1 reports are due on Oct. 5
 - Submit them in your lab section
- ↪ Lab#2 is online
 - This is a hardware lab
 - You must show up to lab for Lab#2
- ↪ Videos online in the lecture chart

Lecture Topics:

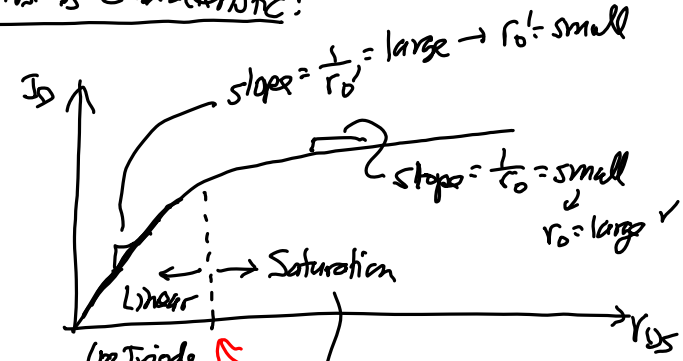
- ↪ Output Swing & Dynamic Range
- ↪ High Swing Current Sources

Last Time: Finished supply independent biasing

Output Swing (Hoodroom)



I_D vs. V_{DS} Characteristic:

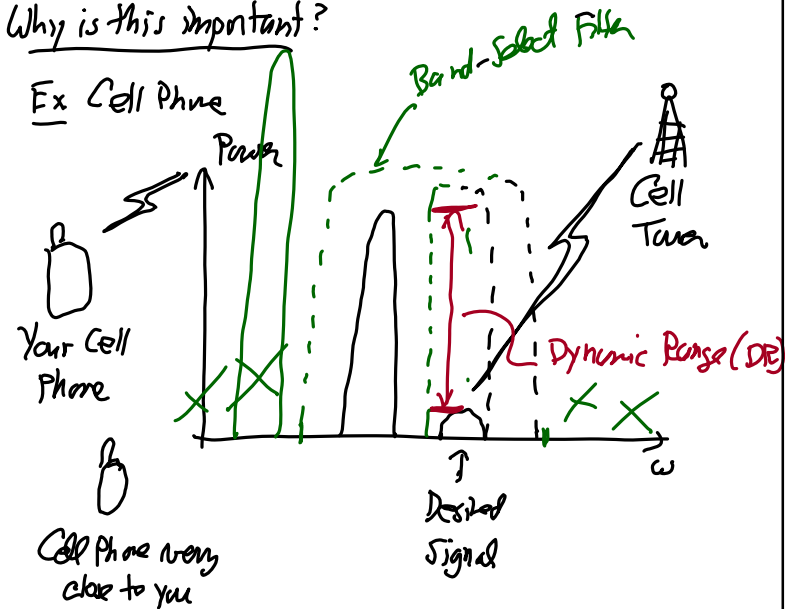


Gain: $g_m r_0' \ll g_m r_0$

$V_{GS} - V_t = V_{ov}$

Much less gain in the triode region than in the saturation region.

Why is this important?



Low Gain \rightarrow can't amplify the desired signal in this low gain time period
caused by the large interfering signal (offset)

Large Gain

This is densitization (swing)
determined by linearity

Dynamic Range (DR) = $\frac{\text{Largest Output Signal}}{\text{minimum signal}}$
determined by noise

What is V_{ov} ?

$$I_D = \frac{1}{2} \mu_n C_{ox} (V_{GS} - V_t)^2$$

$$V_{ov} = \Delta V = V_{DSat} = V_{GS} - V_t = \sqrt{\frac{2I_D}{\mu_n C_{ox} (\frac{W}{L})}} = V_{ov}$$

$\therefore V_{oswing} = V_{DD} - V_{ov1} - V_{ov2} = V_{DD} - 2V_{ov}$
peak-to-peak

What about better current sources? (i.e., high R_o)
 Ex. Cascode Current Source Load & Cascode Drive

\Rightarrow What is the V_{oswing} ?

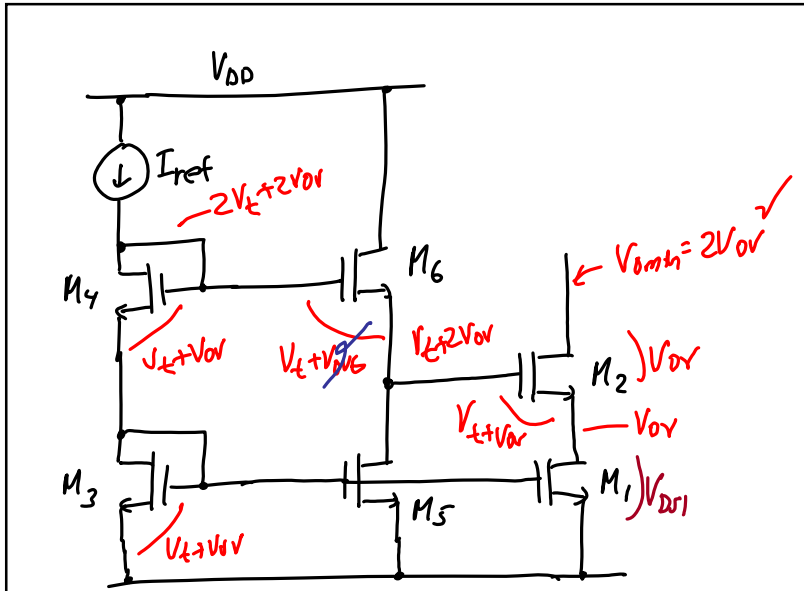
To maintain high gain, all V_{ov} 's $\geq V_{ov}$

$2V_{ov}$

$2V_{ov} = V_{ovmin}$
minimum voltage @ which we still have high gain

$V_{oswing} = V_{DD} - V_{ov1} - V_{ov2} - V_{ov3} - V_{ov4} = V_{DD} - 4V_{ov}$
 $\approx 2 - 4(0.2) = 1$
Best we can do

How do we generate these?
 Answer: make an appropriate V_{BIAS} generator
 simplest way: replica bias \rightarrow use a simple cascode of diodes



All $(\frac{W}{L})_i$'s to same as $(\frac{W}{L})_3$, except $(\frac{W}{L})_6$.

Problem.

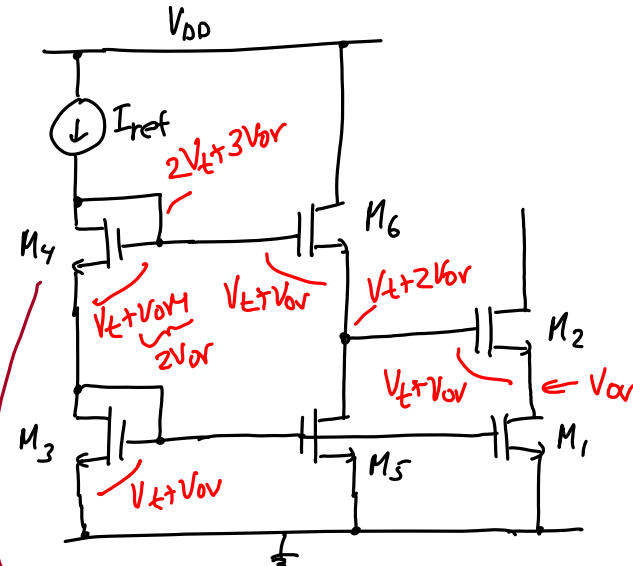
① $(\frac{W}{L})_6$ must be big to send $V_{ov6} \rightarrow DV$

↳ if $(\frac{W}{L})_6$ not big enough $\rightarrow V_{GS6} = V_t + \underbrace{V_{ov6}}_{\text{finite}}$

$$V_{DS1} = V_{ov1} - V_{ov6} < V_{ov1}$$

M_1 not saturated!
(6 is problem)

Another Option: Just accept a $V_t + V_{ov}$ level shift from the gate to source of M_6 .
(use the same ckt.)



Need to design M_4 so that $V_{ov4} = 2V_{ov} = 2V_{ov3}$

$$I_{D3} = \frac{1}{2} \mu_n C_{ox} (\frac{W}{L})_3 (V_{ov3})^2$$

$$I_{D4} = \frac{1}{2} \mu_n C_{ox} (\frac{W}{L})_4 (V_{ov4})^2 = \frac{1}{2} \mu_n C_{ox} (\frac{W}{L})_4 (2V_{ov3})^2$$

$$I_{D3} = I_{D4} = I_{ref}$$

$$\frac{1}{2} \mu_n C_{ox} (\frac{W}{L})_3 (V_{ov3})^2 = \frac{1}{2} \mu_n C_{ox} (\frac{W}{L})_4 (4V_{ov3}^2)$$

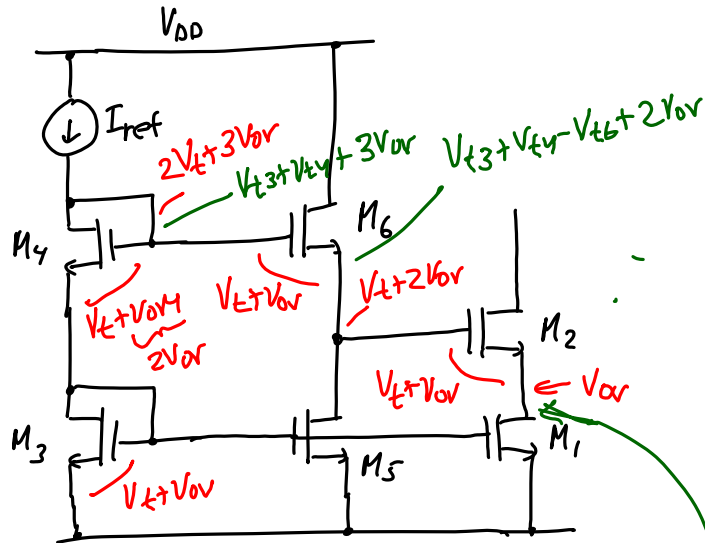
$$\left(\frac{W}{L} \right)_4 = \frac{1}{4} \left(\frac{W}{L} \right)_3 \dots \text{ and } \left(\frac{W}{L} \right)_1 = \left(\frac{W}{L} \right)_2 = \left(\frac{W}{L} \right)_3 = \left(\frac{W}{L} \right)_5 = \left(\frac{W}{L} \right)_6$$

Problem: Body effect in M_4, M_6, M_2 .

$$V_t = V_{t0} + \gamma (\sqrt{2I_{Df1} + |V_{SB1}|} - \sqrt{2I_{Df1}})$$

if $V_{SB} \neq 0 \rightarrow V_t > V_{t0}$

$\therefore V_t$'s of M_4, M_6, M_2 increase.



$$\left. \begin{array}{l} V_{t4} = V_{t6} \rightarrow V_{S4} = V_t + V_{ov} \\ V_{S6} = V_t + 2V_{ov} \end{array} \right\} V_{S6} > V_{S4} \rightarrow V_{t6} > V_{t4}$$

→ Could make $V_{SS1} < V_{ov}$ (trick) ← problem!

← What exactly is this voltage?